# N-Channel 30-V (D-S) MOSFET

## **Key Features:**

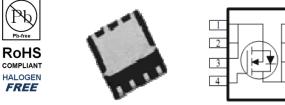
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
VDS (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
30	8.5 @ V <sub>GS</sub> = 10V	20	
- 30	16 @ V <sub>GS</sub> = 4.5V	15	

#### DFN5X6-8L



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage	V <sub>DS</sub>	30	V			
Gate-Source Voltage	age			v		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	-	20	A		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =70°C	I <sub>D</sub>	16			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	50			
Continuous Source Current (Diode Conduction) <sup>a</sup>		ا <sub>s</sub>	6.4	А		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	5	W		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	U 'D	3.2	٧V		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	25	°C/W		
	Steady State	ιν <sub>θ</sub> ja	65	C/W		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit			
Static									
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V			
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$			±100	nA			
Zero Coto Valtore Droin Current		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$		1		uA			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 24 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55^{\circ}\text{C}$			25				
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	30			Α			
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	8.5		8.5	mΩ			
	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_{D} = 12.4 \text{ A}$			16	11122			
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 15 \text{ A}$		15		S			
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 3.2 \text{ A}, V_{GS} = 0 \text{ V}$		0.79		V			
	Dynamic <sup>b</sup>								
Total Gate Charge	Qg	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V,		10					
Gate-Source Charge	$Q_gs$	$V_{DS} = 13 V, V_{GS} = 4.3 V,$ $I_{D} = 15 A$		5.3		nC			
Gate-Drain Charge	$Q_gd$	1 <u>0</u> – 10 A		3.8					
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 15 \text{ V}, \text{ R}_{L} = 1 \Omega,$		6					
Rise Time	t <sub>r</sub>	$V_{DS} = 15 V, K_L - 102,$ $I_D = 15 A,$		6		ns			
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		28					
Fall Time	t <sub>f</sub>	VGEN - 10 V, 1(GEN - 0 12		8					
Input Capacitance	C <sub>iss</sub>			1379					
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		156		pF			
Reverse Transfer Capacitance	C <sub>rss</sub>			116					

#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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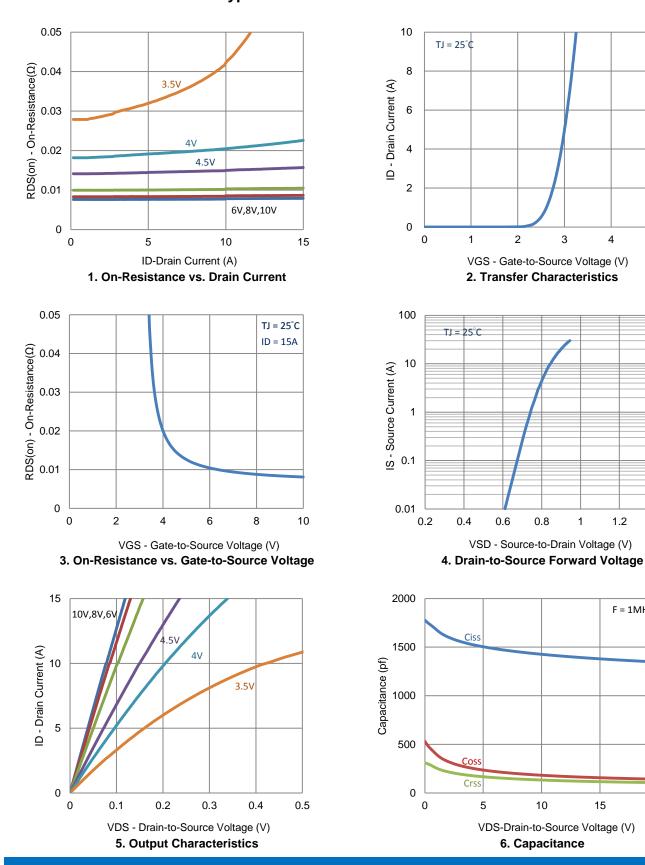
1.2

F = 1MHz

1.4

20

5

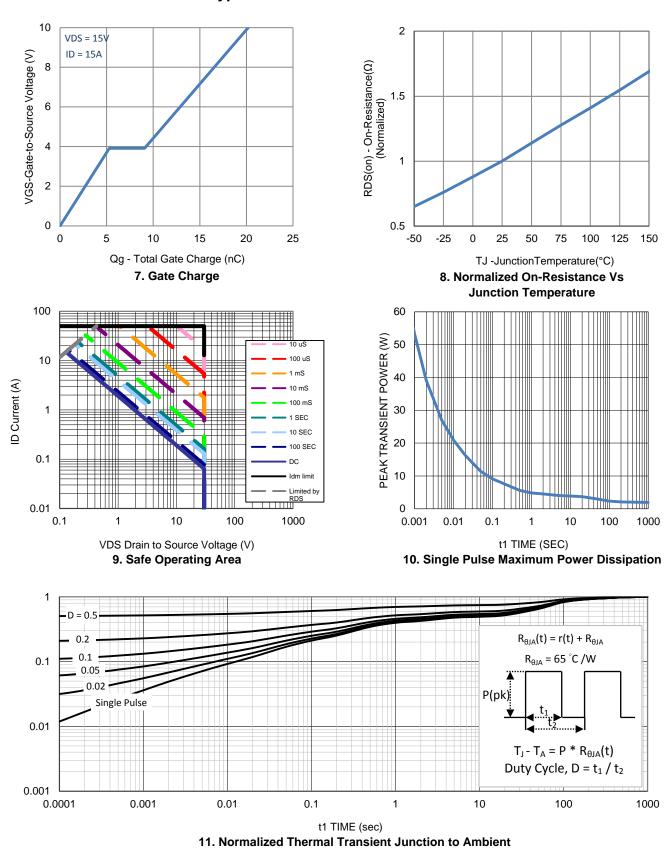


## **Typical Electrical Characteristics**

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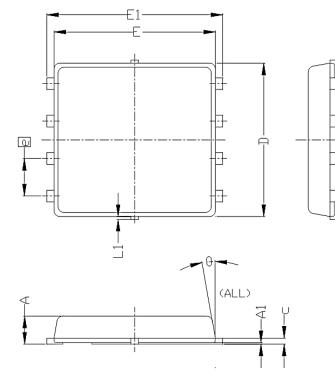
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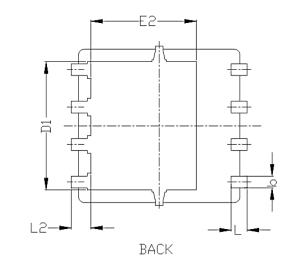
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## **Typical Electrical Characteristics**

## Package Information





SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STNDOLS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0.15	0.20	0.25	0.006	0.008	0.010	
D	5.20 BSC			0.205 BSC			
D1	4.35 BSC			0.171 BSC			
E	5.55 BSC			0.219 BSC			
E1	6.05 BSC			0.238 BSC			
E2	3.62 BSC			0. 143 BSC			
e	1.27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	